

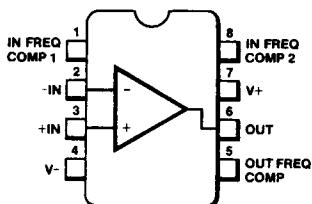
μ A709

High Performance Operational Amplifier

Linear Division Operational Amplifiers

Description

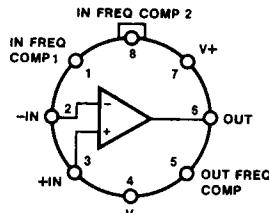
The μ A709 is a monolithic high gain operational amplifier constructed using the Fairchild Planar Epitaxial process. It features low offset, high input impedance, large input common mode range, high output swing under load, and low power consumption. The device displays exceptional temperature stability and will operate over a wide range of supply voltages with little performance degradation. The amplifier is intended for use in DC servo systems, high impedance analog computers, low level instrumentation applications, and for the generation of special linear and nonlinear transfer functions.

Connection Diagram**8-Lead DIP and SO-8 Package
(Top View)**

CD00731F

Order Information

Device Code	Package Code	Package Description
μ A709TC	9T	Molded DIP
μ A709SC	KC	Molded Surface Mount

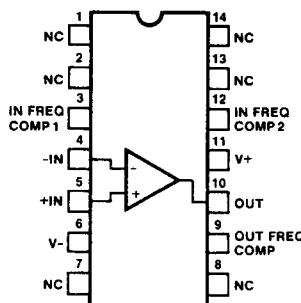
Connection Diagram**8-Lead Metal Package
(Top View)**

CD00721F

Lead 4 connected to case

Order Information

Device Code	Package Code	Package Description
μ A709AHM	5W	Metal
μ A709HM	5W	Metal
μ A709HC	5W	Metal

Connection Diagram**14-Lead DIP
(Top View)**

CD00741F

Order Information

Device Code	Package Code	Package Description
μ A709PC	9A	Molded DIP

Absolute Maximum Ratings

Storage Temperature Range

Metal Can	-65°C to +175°C
Molded DIP and SO-8	-65°C to +150°C

Operating Temperature Range

Extended (μ A709AM, μ A709M)	-55°C to +125°C
Commercial (μ A709C)	0°C to +70°C

Lead Temperature

Metal Can (soldering, 60 s)	300°C
Molded DIP and SO-8 (soldering, 10s)	265°C

Internal Power Dissipation^{1, 2}

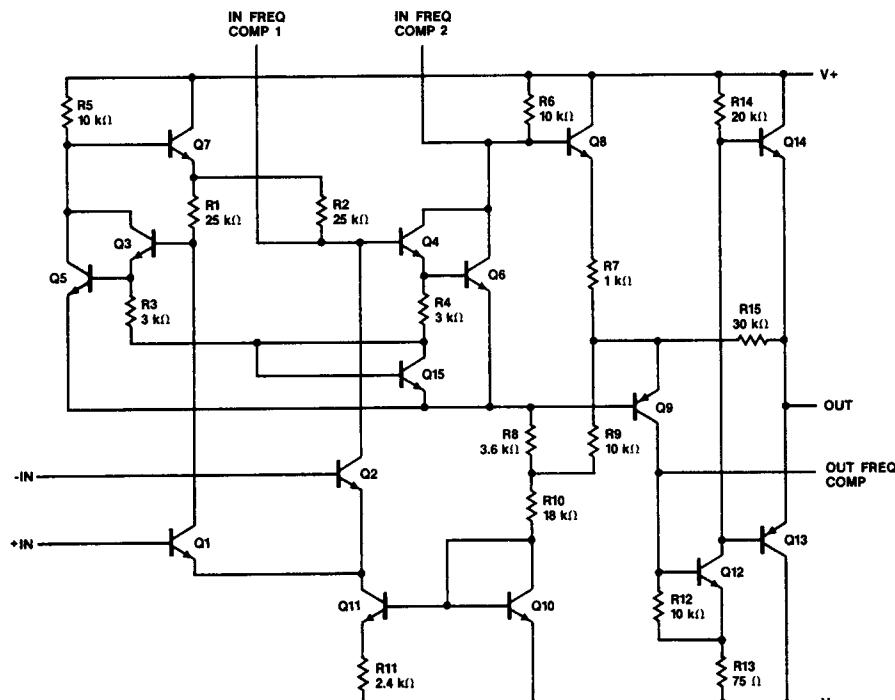
8L-Metal Can	1.00 W
8L-Molded DIP	0.93 W
SO-8	0.81 W
14L-Molded DIP	1.04 W
Supply Voltage	± 18 V
Differential Input Voltage	± 5.0 V
Input Voltage	± 10 V
Output Short Circuit Duration	5.0 s

Notes

1. T_J Max = 150°C for the Molded DIP and SO-8, and 175°C for the Metal Can.

2. Ratings apply to ambient temperature at 25°C. Above this temperature, derate the 8L-Metal Can at 6.7 mW/°C, the 8L-Molded DIP at 7.5 mW/°C, the SO-8 at 6.5 mW/°C, and the 14L-Molded DIP at 8.3 mW/°C.

Equivalent Circuit



EC00151F

μ A709

μ A709A and μ A709

Electrical Characteristics $T_A = 25^\circ\text{C}$, $\pm 9.0 \text{ V} \leq V_{CC} \leq \pm 15 \text{ V}$, unless otherwise specified.

Symbol	Characteristic	Condition	μ A709A			μ A709			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		0.6	2.0		1.0	5.0	mV
I_{IO}	Input Offset Current			10	50		50	200	nA
I_{IB}	Input Bias Current			100	200		200	500	nA
Z_I	Input Impedance		350	700		150	400		k Ω
I_{CC}	Supply Current	$V_{CC} = \pm 15 \text{ V}$		2.5	3.6		2.7	5.5	mA
P_c	Power Consumption	$V_{CC} = \pm 15 \text{ V}$		75	108		80	165	mW
TR	Transient Response	Rise time	$V_{CC} = \pm 15 \text{ V}$ $V_I = 20 \text{ mV}$ $R_L = 2.0 \text{ k}\Omega$ $C_1 = 5.0 \text{ nF}$ $A_V = 1.0$		0.3	1.5		0.3	1.0
		Overshoot	$R_2 = 50 \text{ }\Omega$ $C_L \leq 100 \text{ pF}$ $R_1 = 1.5 \text{ k}\Omega$ $C_2 = 200 \text{ pF}$ $A_V = 1.0$		10	30		10	30

The following specifications apply over the range of -55°C to $+125^\circ\text{C}$ for the μ A709A and μ A709.

V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			3.0			6.0	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Sensitivity	$R_S = 50 \text{ }\Omega$		1.8	10		3.0		$\mu\text{V}/^\circ\text{C}$
		$R_S \leq 10 \text{ k}\Omega$		4.8	25		6.0		
I_{IO}	Input Offset Current	$T_A = +125^\circ\text{C}$		3.5	50		20	200	nA
		$T_A = -55^\circ\text{C}$		40	250		100	500	
$\Delta I_{IO}/\Delta T$	Input Offset Current Temperature Sensitivity	$T_A = +25^\circ\text{C}$ to $+125^\circ\text{C}$		0.08	0.5				$\text{nA}/^\circ\text{C}$
		$T_A = +25^\circ\text{C}$ to -55°C		0.45	2.8				
I_{IB}	Input Bias Current	$T_A = -55^\circ\text{C}$		300	600		500	1500	nA
$\Delta I_{IB}/\Delta T$	Input Bias Current Temperature Sensitivity	$T_A = +125^\circ\text{C}$		2.1	3.0				$\text{nA}/^\circ\text{C}$
		$T_A = -55^\circ\text{C}$		2.7	4.5				
Z_I	Input Impedance	$T_A = -55^\circ\text{C}$	85	170		40	100		k Ω
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$	80	110		70	90		db
V_{IR}	Input Voltage Range	$V_{CC} = \pm 15 \text{ V}$	± 8.0	± 10		± 8.0	± 10		V
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		40	100		50	150	$\mu\text{V}/\text{V}$
Avs	Large Signal Voltage Gain	$V_{CC} = \pm 15 \text{ V}$ $R_L \geq 2.0 \text{ k}\Omega$ $V_O = \pm 10 \text{ V}$	25		70	25	45	70	V/mV
V_{OP}	Output Voltage Swing	$V_{CC} = \pm 15 \text{ V}$ $R_L = 10 \text{ k}\Omega$	± 12	± 14		± 12	± 14		V
		$V_{CC} = \pm 15 \text{ V}$ $R_L = 2.0 \text{ k}\Omega$	± 10	± 13		± 10	± 13		

μ A709

μ A709A and μ A709 (Cont.)

Electrical Characteristics $T_A = 25^\circ\text{C}$, $\pm 9.0 \text{ V} \leq V_{CC} \leq \pm 15 \text{ V}$, unless otherwise specified.

Symbol	Characteristic	Condition	μ A709A			μ A709			Unit
			Min	Typ	Max	Min	Typ	Max	
I_{CC}	Supply Current	$T_A = \pm 125^\circ\text{C}$		2.1	3.0				mA
		$T_A = -55^\circ\text{C}$		2.7	4.5				

μ A709C

Electrical Characteristics $T_A = 25^\circ\text{C}$, $V_{CC} = \pm 15 \text{ V}$, unless otherwise specified.

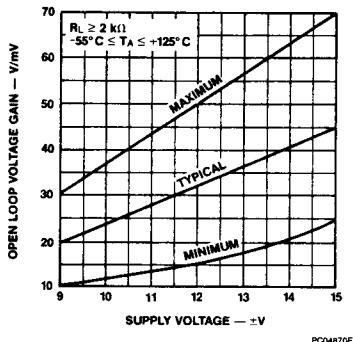
Symbol	Characteristic	Condition	μ A709C			Unit	
			Min	Typ	Max		
V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$		2.0	7.5	mV	
I_{IO}	Input Offset Current			100	500	nA	
I_{IB}	Input Bias Current			300	1500	nA	
Z_I	Input Impedance		50	250		k Ω	
I_{CC}	Supply Current	$V_{CC} = \pm 15 \text{ V}$		2.7	6.66	mA	
P_c	Power Consumption	$V_{CC} = \pm 15 \text{ V}$		80	200	mW	
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$	65	90		dB	
V_{IR}	Input Voltage Range	$V_{CC} = \pm 15 \text{ V}$	± 8.0	± 10		V	
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		50	200	μ V/V	
TR	Transient Response	Rise time	$V_{CC} = \pm 15 \text{ V}$ $V_I = 20 \text{ mV}$ $R_L = 2.0 \text{ k}\Omega$ $C_1 = 5.0 \text{ nF}$ $A_V = 1.0$		0.3		μ s
		Overshoot	$R_2 = 50 \text{ }\Omega$ $C_L = 100 \text{ pF}$ $R_1 = 1.5 \text{ k}\Omega$ $C_2 = 200 \text{ pF}$ $A_V = 1.0$		10		%

The following specifications apply over the range of 0°C to $+70^\circ\text{C}$.

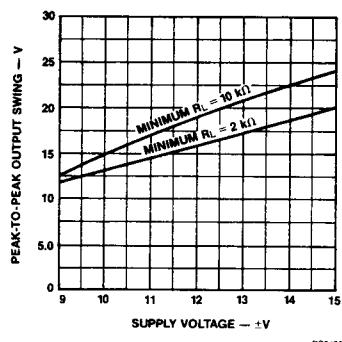
V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			10.0	mV
I_{IO}	Input Offset Current	$T_A = 0^\circ\text{C}$			750	nA
I_{IB}	Input Bias Current	$T_A = 0^\circ\text{C}$			2000	nA
Z_I	Input Impedance	$T_A = 0^\circ\text{C}$	35	80		k Ω
A_{VS}	Large Signal Voltage Gain	$V_{CC} = \pm 15 \text{ V}$ $R_L \geq 2.0 \text{ k}\Omega$ $V_O = \pm 10 \text{ V}$	15	45		V/mV
V_{OP}		$V_{CC} = \pm 15 \text{ V}$ $R_L = 10 \text{ k}\Omega$	± 12	± 14		V
		$V_{CC} = \pm 15 \text{ V}$ $R_L = 2.0 \text{ k}\Omega$	± 10	± 13		V

Typical Performance Curves for μ A709A

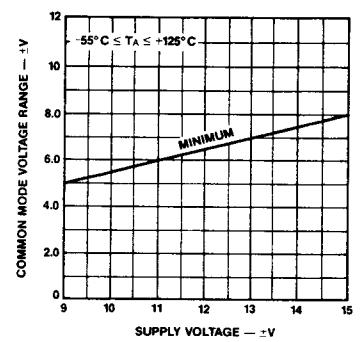
Voltage Gain vs Supply Voltage



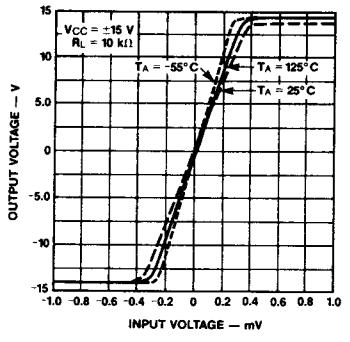
Output Voltage Swing vs Supply Voltage



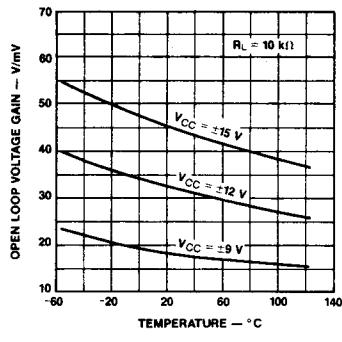
Input Common Mode Voltage Range vs Supply Voltage



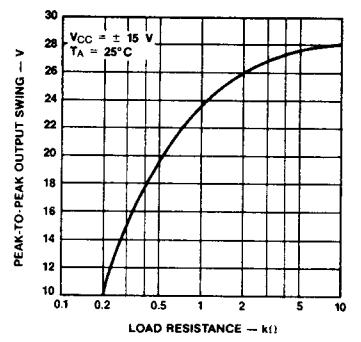
Voltage Transfer Characteristics



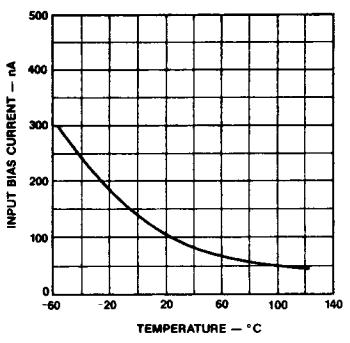
Voltage Gain vs Temperature



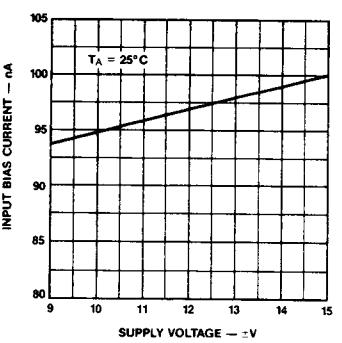
Output Voltage Swing vs Load Resistance



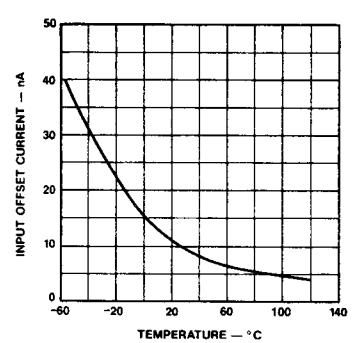
Input Bias Current vs Temperature



Input Bias Current vs Supply Voltage

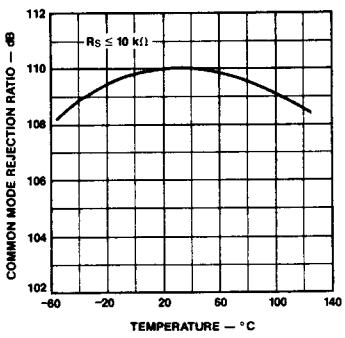


Input Offset Current vs Temperature

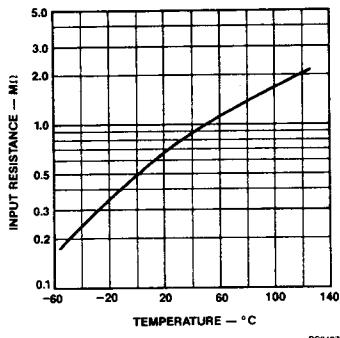


Typical Performance Curves for μ A709A (Cont.)

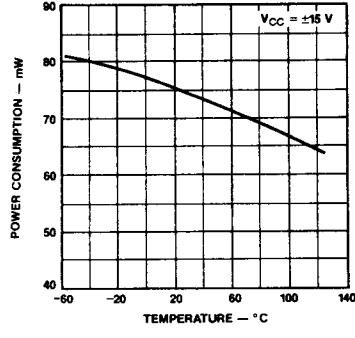
Common Mode Rejection Ratio vs Temperature



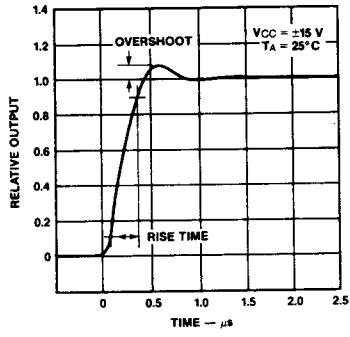
Input Resistance vs Temperature



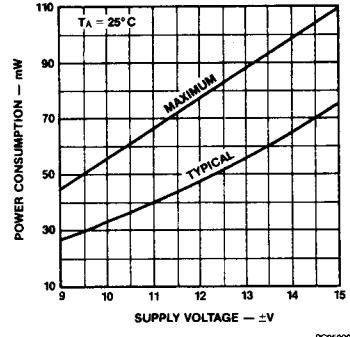
Power Consumption vs Temperature



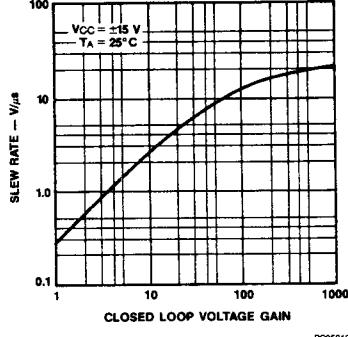
Transient Response



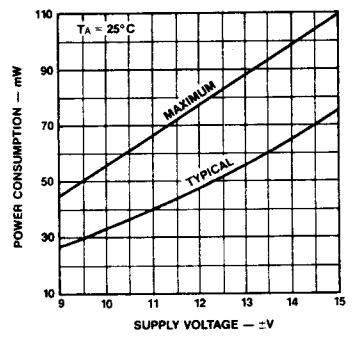
Power Consumption vs Supply Voltage



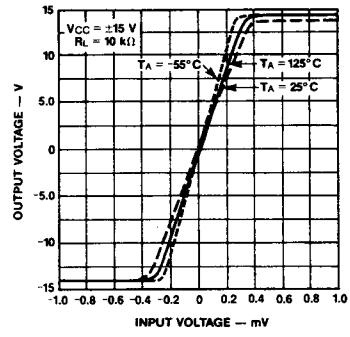
Slew Rate vs Closed Loop Gain Using Recommended Compensation Networks



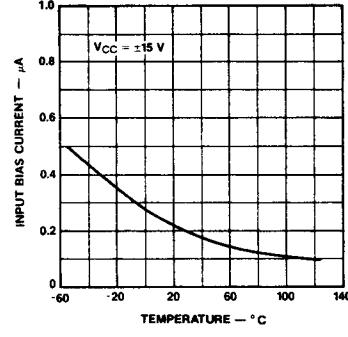
Power Consumption vs Supply Voltage (μ A709 and μ A709C)



Voltage Transfer Characteristics (μ A709 and μ A709C)

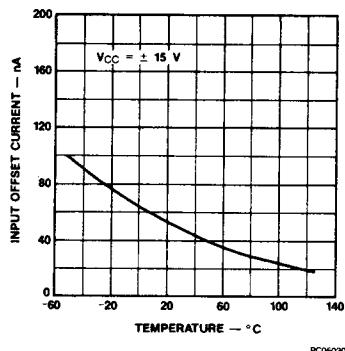


Input Bias Current vs Temperature (μ A709 and μ A709C)

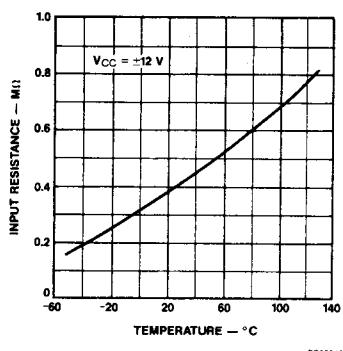


Typical Performance Curves for μ A709 and μ A709C (Cont.)

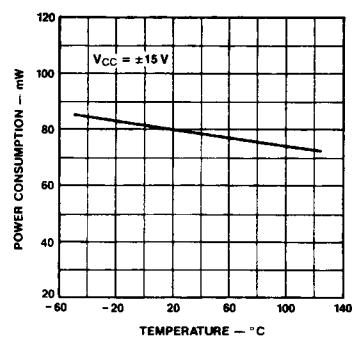
Input Offset Current vs Temperature



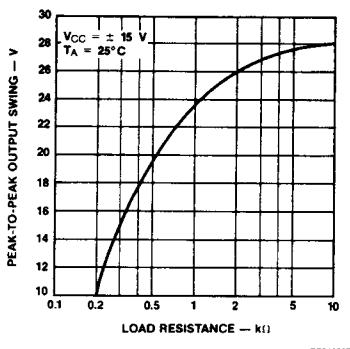
Input Resistance vs Temperature



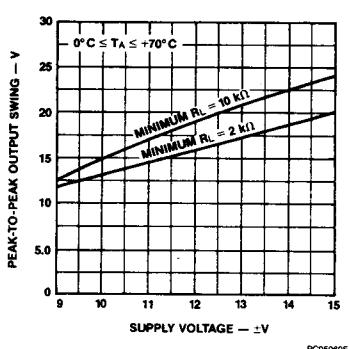
Power Consumption vs Temperature



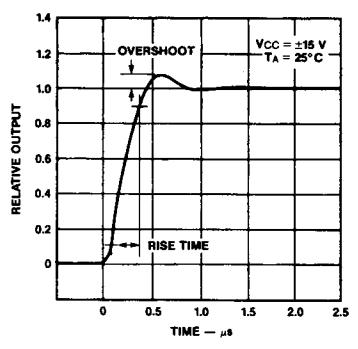
Output Voltage Swing vs Load Resistance



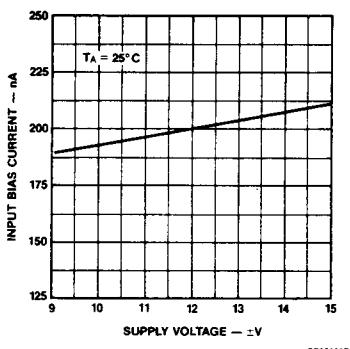
Output Voltage Swing vs Supply Voltage



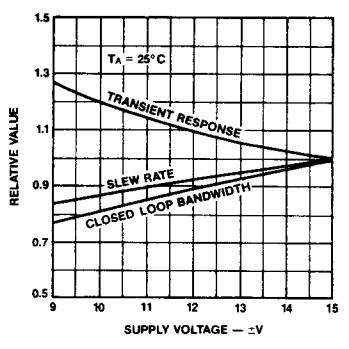
Transient Response



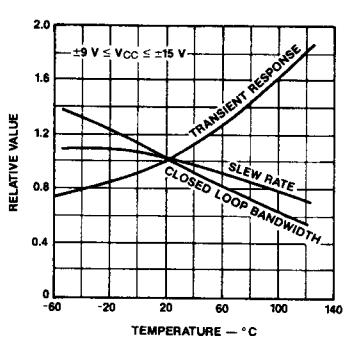
Input Bias Current vs Supply Voltage



Frequency Characteristics vs Supply Voltage

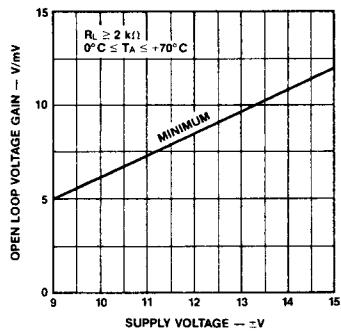


Frequency Characteristics vs Temperature



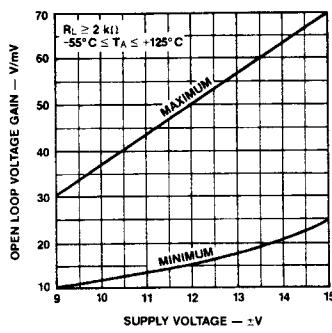
Typical Performance Curves for μA709 and μA709C (Cont.)

Voltage Gain vs Supply Voltage (μA709C)



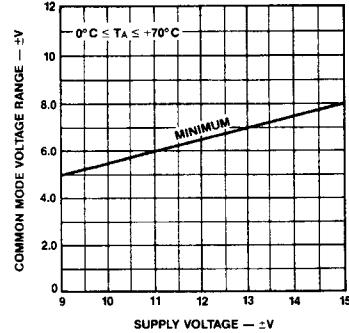
PC05100F

Voltage Gain vs Supply Voltage (μA709)



PC05110F

Input Common Mode Voltage Range vs Supply Voltage

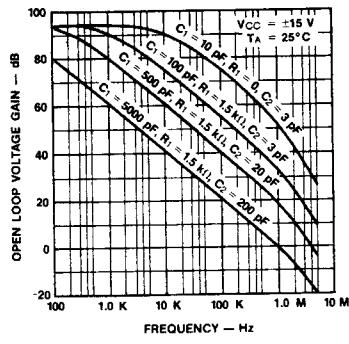


PC05121F

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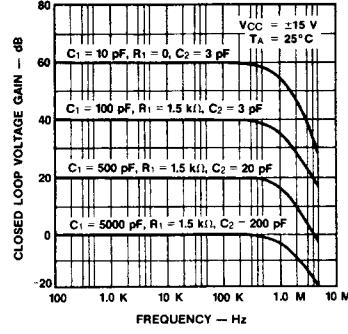
Frequency Compensation Curves For All Types

Open Loop Frequency Response For Various Values Of Compensation



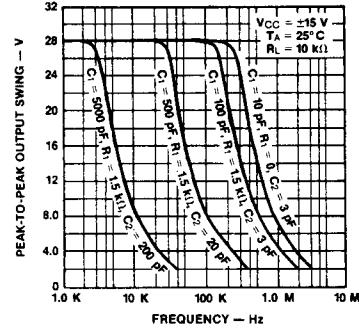
PC05131F

Frequency Response For Various Closed Loop Gains



PC05141F

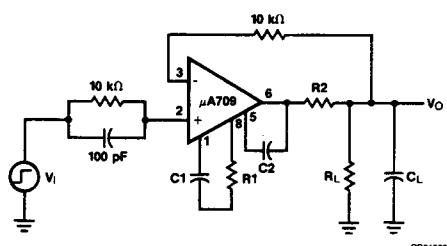
Output Voltage Swing vs Frequency For Various Values Of Compensation



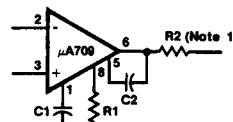
PC05151F

Test Circuits

Transient Response Circuit

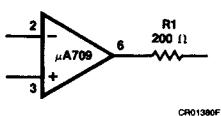


Frequency Compensation Circuit

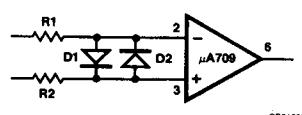


Protection Circuits

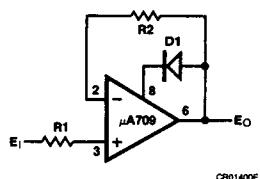
Output Short Circuit Protection



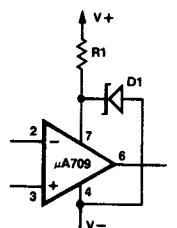
Input Breakdown Protection



Latch Up Protection



Supply Over Voltage Protection



Note

1. Use $R2 = 50 \Omega$ when the amplifier is operated with capacitive loading.